

ABSTRACT OF THE DISCLOSURE

It is an object to provide a p-type ZnS based semiconductor material having a low resistance which can easily form an ohmic contact to a metallic material. Moreover, the invention provides a semiconductor device and a semiconductor light emitting device which include an electrode having a low resistance on a substrate other than a single crystal substrate, for example, a glass substrate.

The semiconductor material according to the invention is used as a hole injecting electrode layer of a light emitting device and has a transparent property in a visible region which is expressed in a composition formula of $\text{Zn}_{(1-\alpha-\beta-\gamma)}\text{Cu}_\alpha\text{Mg}_\beta\text{Cd}_\gamma\text{S}_{(1-x-y)}\text{Se}_x\text{Te}_y$ ($0.004 \leq \alpha \leq 0.4$, $\beta \leq 0.2$, $\gamma \leq 0.2$, $0 \leq x \leq 1$, $0 \leq y \leq 0.2$, and $x + y \leq 1$).